



Bipolar PNP Bare Die – BTP6025

Part Description

The BTP6025 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6024.

Key Parameters:

- VCBO = -50V
- VCEO = -50V
- VEBO = -7V
- hFE = 200-500 @ VCE = -2V, IC = -0.3A
- VCE(Sat) = -0.2V @ IC = -1A, IB = -33mA
- fT = 180 MHz @ VCE = -2V, IE = 0A
- COBO = 20pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to TOSHIBA 2SA2060

Die Size (Unawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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